

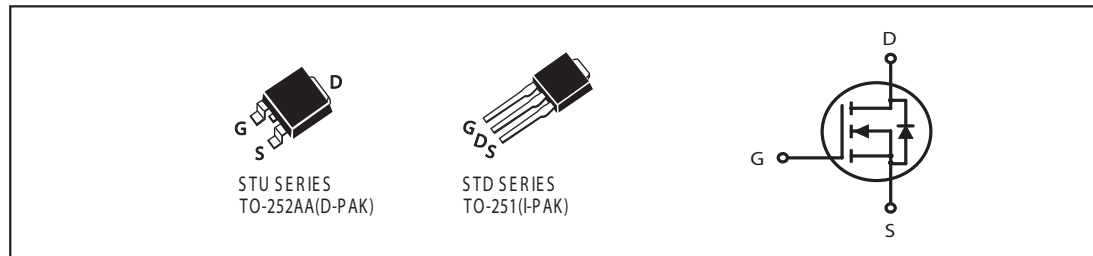


## N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DS(ON)</sub> (mΩ) Max
40V	24A	24 @ V <sub>GS</sub> = 10V
		30 @ V <sub>GS</sub> = 4.5V

### FEATURES

- Super high dense cell design for low R<sub>DS(ON)</sub>.
- Rugged and reliable.
- TO-252 and TO-251 Package.



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	40	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous <sup>a</sup> @ T <sub>C</sub> =25°C -Pulsed <sup>b</sup>	I <sub>D</sub>	24	A
	I <sub>DM</sub>	75	A
Drain-Source Diode Forward Current	I <sub>S</sub>	8	A
Maximum Power Dissipation @ T <sub>C</sub> =25°C	P <sub>D</sub>	50	W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 175	°C

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	3	°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	50	°C/W

# STU/D420S

ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250uA	40			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 32V, V <sub>GS</sub> = 0V			1	uA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±10	uA
<b>ON CHARACTERISTICS<sup>a</sup></b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250uA	1	1.9	3	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A		17	24	m ohm
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 8A		23.5	30	m ohm
On-State Drain Current	I <sub>D(ON)</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 10V	30			A
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 10A		16		S
<b>DYNAMIC CHARACTERISTICS<sup>b</sup></b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V f = 1.0MHz		750		pF
Output Capacitance	C <sub>OSS</sub>			110		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			65		pF
Gate resistance	R <sub>g</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V, f = 1.0MHz		3		ohm
<b>SWITCHING CHARACTERISTICS<sup>b</sup></b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> = 15V I <sub>D</sub> = 1 A V <sub>GS</sub> = 10V R <sub>GEN</sub> = 3 ohm		13		ns
Rise Time	t <sub>r</sub>			10		ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>			37		ns
Fall Time	t <sub>f</sub>			12		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 20V, I <sub>D</sub> = 10A, V <sub>GS</sub> = 10V		15		nC
		V <sub>DS</sub> = 20V, I <sub>D</sub> = 10A, V <sub>GS</sub> = 4.5V		7		nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> = 20V, I <sub>D</sub> = 10A		2.5		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> = 10V		4		nC

# STU/D420S

## ELECTRICAL CHARACTERISTICS ( $T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>DRAIN-SOURCE DIODE CHARACTERISTICS <sup>a</sup></b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_s = 8A$		0.84	1.3	V

### Notes

- a. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

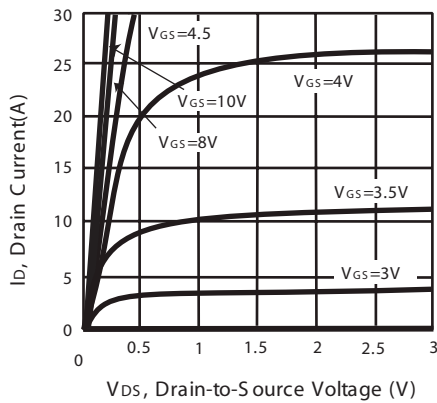


Figure 1. Output C characteristics

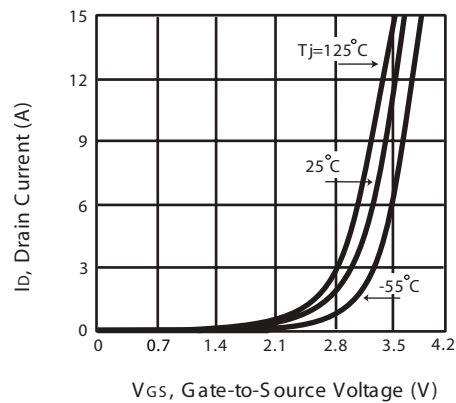


Figure 2. Transfer C characteristics

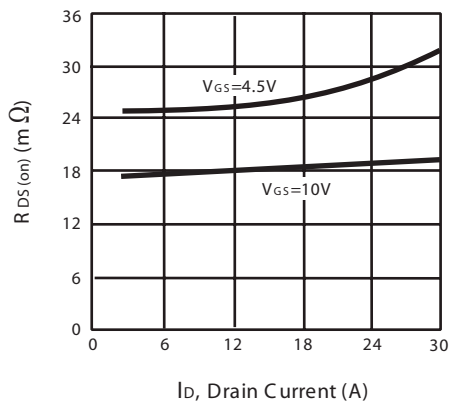


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

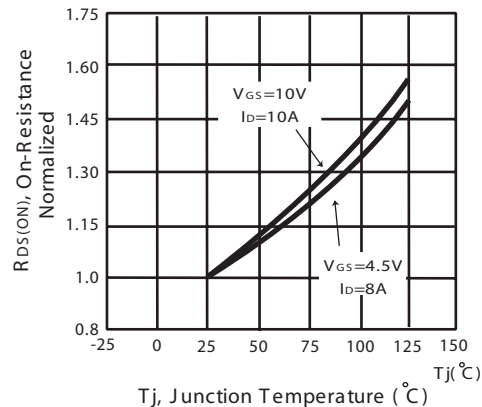


Figure 4. On-Resistance Variation with Drain Current and Temperature

# STU/D420S

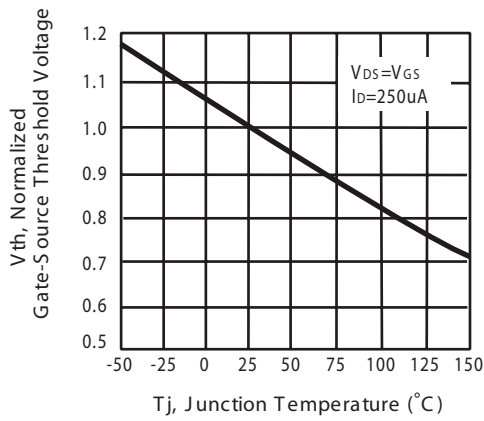


Figure 5. Gate Threshold Variation with Temperature

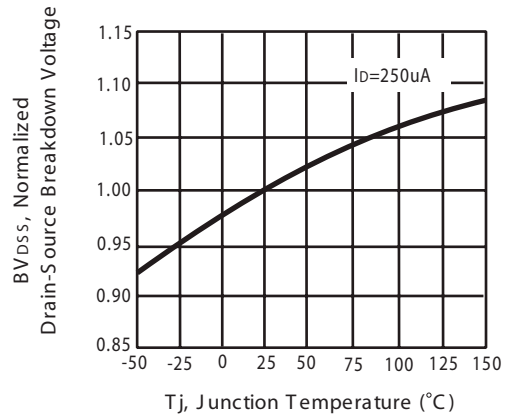


Figure 6. Breakdown Voltage Variation with Temperature

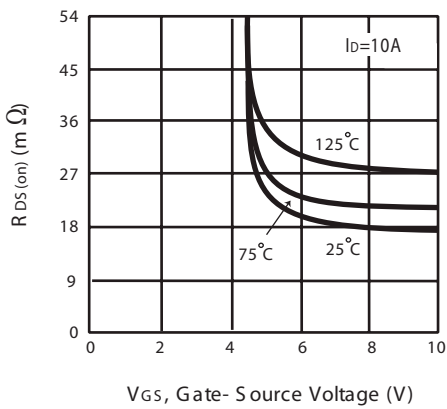


Figure 7. On-Resistance vs. Gate-Source Voltage

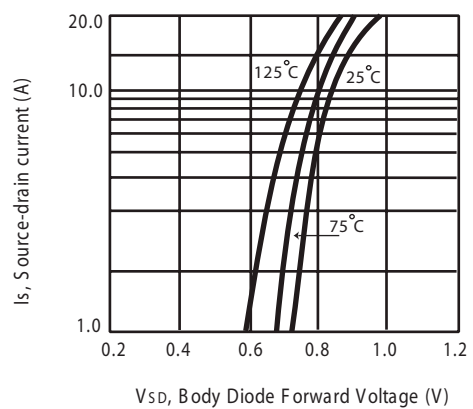


Figure 8. Body Diode Forward Voltage Variation with Source Current

# STU/D420S

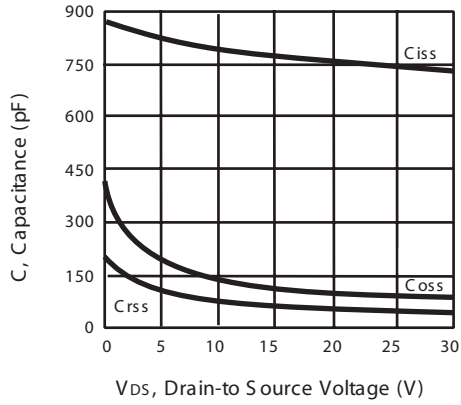


Figure 9. Capacitance

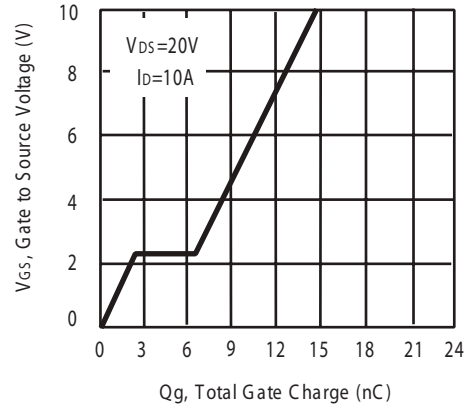


Figure 10. Gate Charge

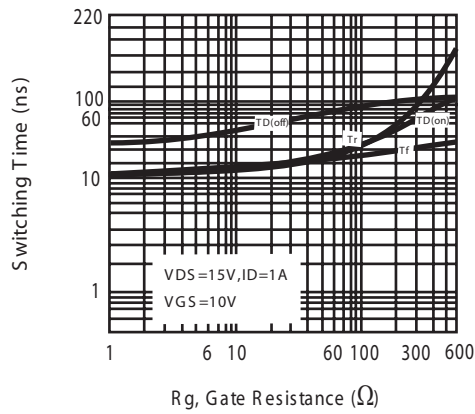


Figure 11. switching characteristics

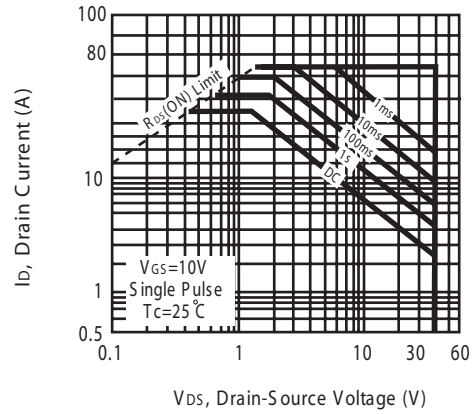


Figure 12. Maximum Safe Operating Area

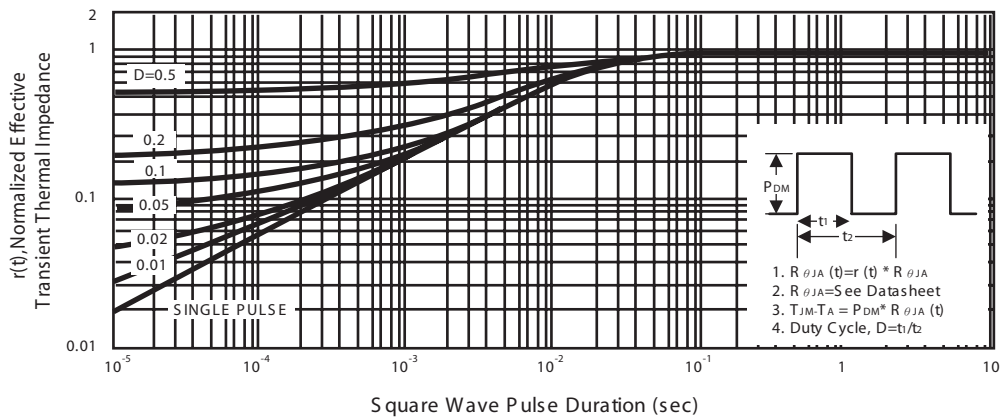
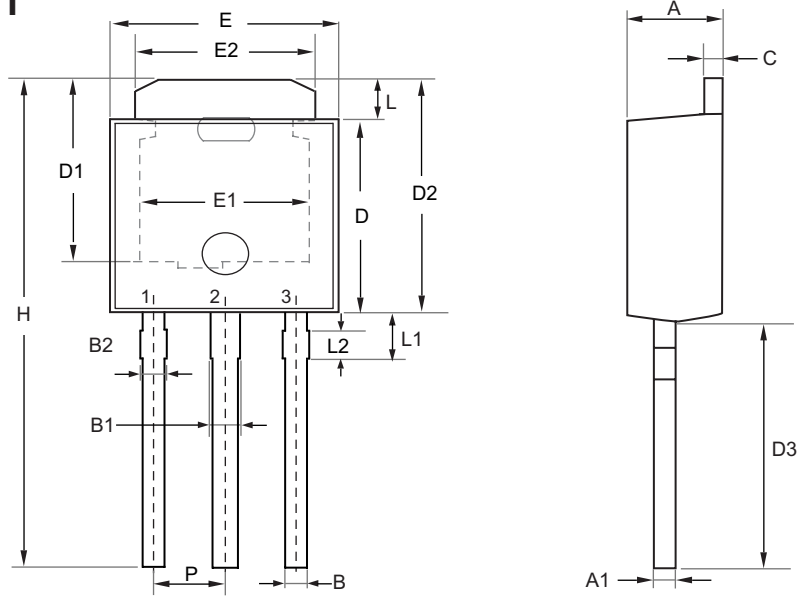


Figure 13. Normalized Thermal Transient Impedance Curve

# STU/D420S

## PACKAGE OUTLINE DIMENSIONS

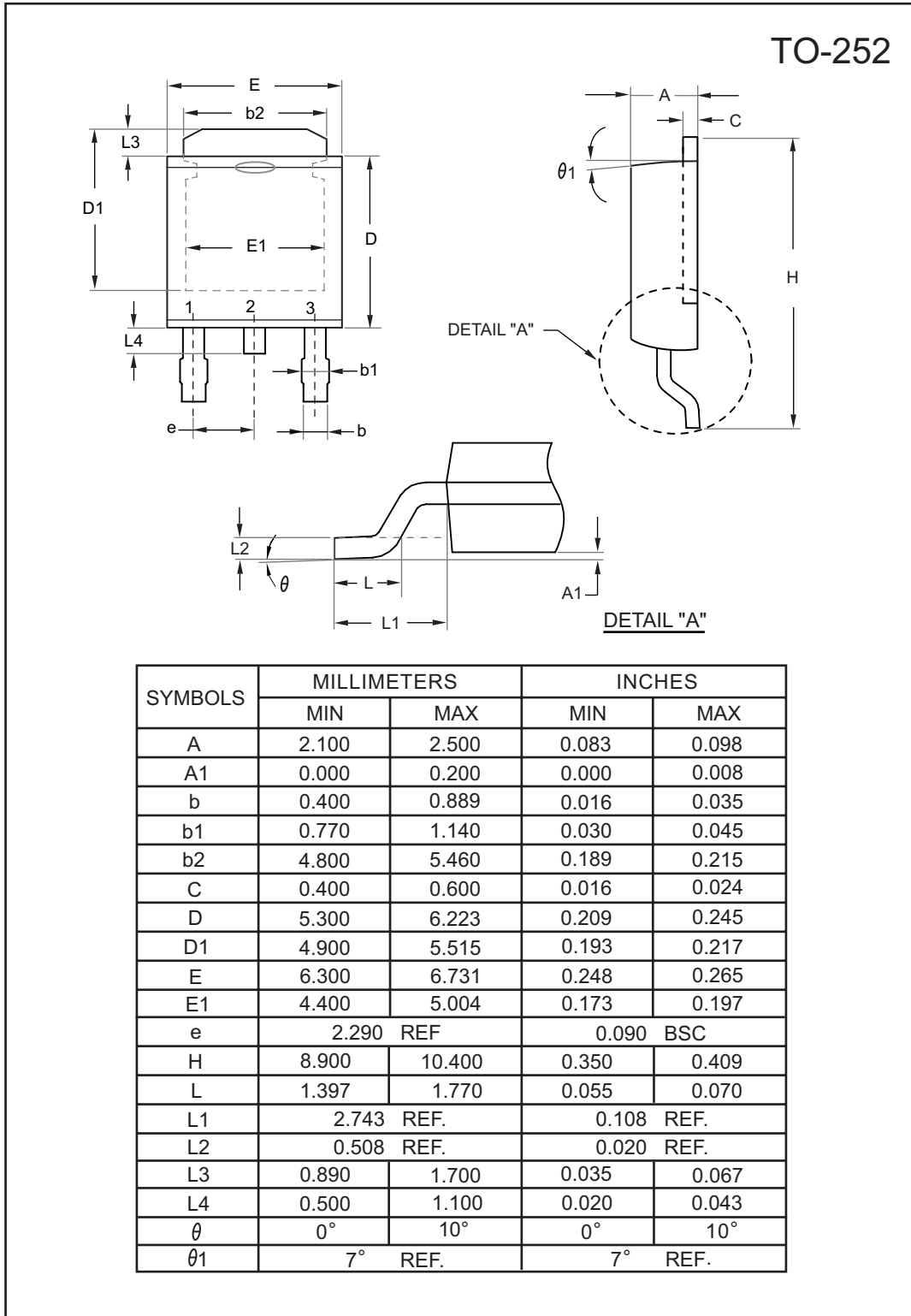
TO-251



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.350	0.650	0.014	0.026
B	0.400	0.800	0.016	0.031
B1	0.650	1.050	0.026	0.041
B2	0.500	0.900	0.020	0.035
C	0.400	0.600	0.016	0.024
D	5.300	5.700	0.209	0.224
D1	4.900	5.300	0.193	0.209
D2	6.700	7.300	0.264	0.287
D3	7.000	8.000	0.276	0.315
H	13.700	15.300	0.539	0.602
E	6.300	6.700	0.248	0.264
E1	4.600	4.900	0.181	0.193
E2	4.800	5.200	0.189	0.205
L	1.300	1.700	0.051	0.067
L1	1.400	1.800	0.055	0.071
L2	0.500	0.900	0.020	0.035
P	2.300 BSC		0.091 BSC	

# STU/D420S

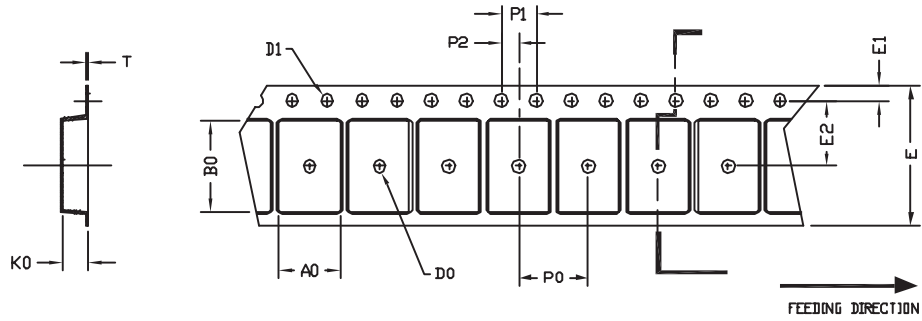
## PACKAGE OUTLINE DIMENSIONS



# STU/D420S

## TO-252 Tape and Reel Data

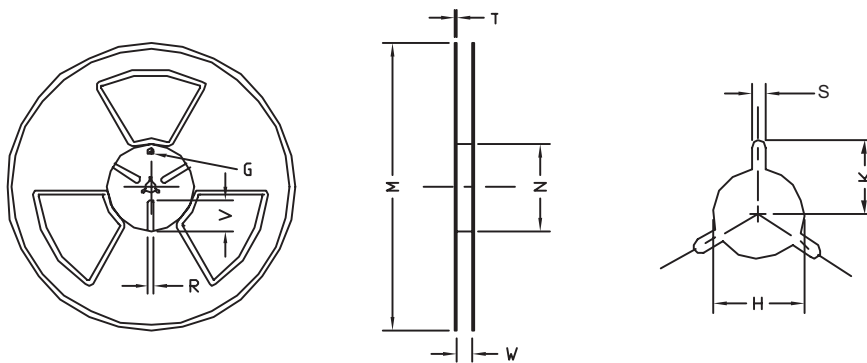
### TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.80 ±0.1	10.3 ±0.1	2.50 ±0.1	φ2	φ1.5 +0.1 -0	16.0 0.3±	1.75 0.1±	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

### TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---